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- (71) **Applicant: APPLIED MATERIALS, INC.** [US/US];
3050 Bowers Avenue, Santa Clara, California 95054 (US).
- (72) **Inventors: CHEN, Yihong;** 1192 Fynes Ct., San Jose, California 95131 (US). **CHAN, Kelvin;** 1740 Blakesley Dr, San Ramon, California 94582 (US). **LU, Xinliang;** 45 Japala Court, Fremont, California 94539 (US). **GANDIKOTA, Srinivas;** 2727 Monroe Street, Santa Clara, California 95051 (US). **WU, Yong;** 1271 Lakeside Dr., Apt 2138, Sunnyvale, California 94085 (US). **ROY, Susmit Singha;** 1000 Escalon Avenue, Apt. E1033, Sunnyvale, California 94085 (US). **CHIN, Chia Cheng;** 700 Agnew Rd., Apt. 366, Santa Clara, California 95054 (US).
- (74) **Agent: WHITNEY, Karen M.;** Servilla Whitney LLC, 33 Wood Avenue South, Suite 830, Iselin, New Jersey 08830 (US).
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(54) **Title:** NUCLEATION-FREE GAP FILL ALD PROCESS

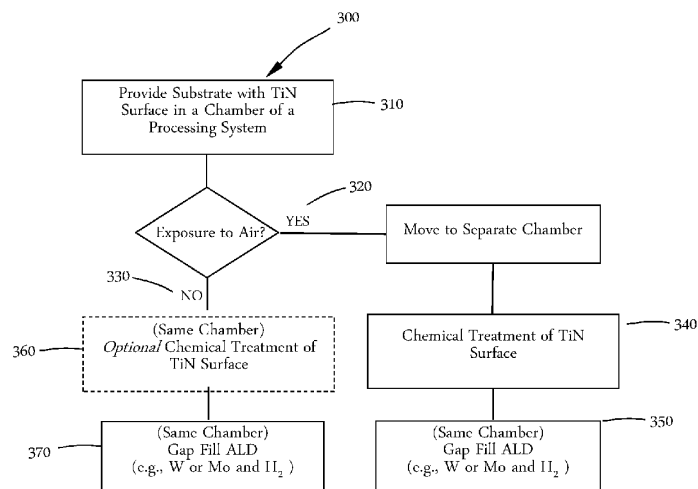


FIG. 6

(57) **Abstract:** Processing methods comprise forming a gap fill layer comprising tungsten or molybdenum by exposing a substrate surface having at least one feature thereon sequentially to a metal precursor and a reducing agent comprising hydrogen to form the gap fill layer in the feature, wherein there is not a nucleation layer between the substrate surface and the gap fill layer.

[Continued on next page]

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